

DESCRIPTION

The MMBT2222AL is available in SOT-23 package.

FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available (MMBT2907A)
- Available in SOT-23 package

ORDERING INFORMATION

Package Type	Part Number	
SOT-23	MMBT2222AL	
Note	SPQ: 3,000pcs/Reel	
AiT provides all RoHS Compliant Products		

PIN DESCRIPTION



PIN#	DESCRIPTION	
В	BASE	
Е	EMITTER	
С	COLLECTOR	

ABSOLUTE MAXIMUM RATINGS

T _A =25°C, unless otherwise noted	
VCBO, Collector-Base Voltage	75V
V _{CEO} , Collector-Emitter Voltage	40V
V _{EBO} , Emitter-Base Voltage	6V
Ic, Collector Current -Continuous	600mA
P _c , Collector Dissipation	250mW
R _{0JA} , Thermal Resistance, Junction to Ambient	500°C/W
T _J , Junction Temperature	150°C
T _{STG} , Storage Temperature	-55 ~ +150°C

Stresses above may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics are not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



ELECTRICAL CHARACTERISTICS

T_A=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	V _{(BR)CBO}	Ic= 10μΑ, I _E =0	75	-	-	V
Collector-Emitter Breakdown Voltage	V(BR)CEO*	Ic= 10mA, Iв=0	40	-	-	V
Emitter-Base Breakdown Voltage	V(BR)EBO	I _E =10μΑ, I _C =0	6	-	-	V
Collector Cut-Off Current	I _{CBO}	V _{CB} =60V, I _E =0	-	-	0.01	μA
Collector Cut-Off Current	ICEX	V _{CE} =30V, V _{BE (off)} =3V	-	-	0.01	μA
Emitter Cut-Off Current	I _{EBO}	V _{EB} = 3V, I _C =0	-	-	0.1	μA
DC Current Gain	h _{FE*}	V _{CE} =10V, I _C = 150mA	100	-	300	
	hfe	V _{CE} =10V, I _C = 0.1mA	35	-	-	
	h _{FE*}	V _{CE} =10V, I _C = 500mA	40	-	-	
Collector-Emitter Saturation Voltage	V _{CE (sat)*}	Ic=500 mA, I _B = 50mA	-	-	1.0	v
		lc=150mA, l _B =15mA	-	-	0.3	
Base-Emitter Saturation Voltage	V _{BE (sat)*}	Ic=500 mA, I _B = 50mA	-	-	2.0	v
		I_{C} =150mA, I_{B} =15mA	-	-	1.2	
Transition Frequency	f⊤	V _{CE} =20V, I _C = 20mA, f=100MHz	300	-	-	MHz
Delay Time	td	V _{CC} =30V, V _{BE (off)} =-0.5V	-	-	10	
Rise Time	tr	Ic=150mA, I _{B1} = 15mA	-	-	25	ns
Storage Time	ts	Vcc=30V, Ic=150mA	-	-	225	
Fall Time	t _f	I _{B1} =-I _{B2} =15mA	-	-	60	115

*pulse test: Pulse Width ≤300µs, Duty Cycle≤ 2.0%.



TYPICAL CHARACTERISTICS









PACKAGE INFORMATION

Dimension in SOT-23 Package (Unit: mm)







Symbol	Min.	Max.		
A	0.900	1.400		
В	1.780	2.050		
bp	0.350	0.510		
С	0.080	0.190		
D	2.700	3.100		
E	1.200	1.650		
HE	2.100	3.000		
A ₁	0.013	0.100		
Lp	0.200	0.500		





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